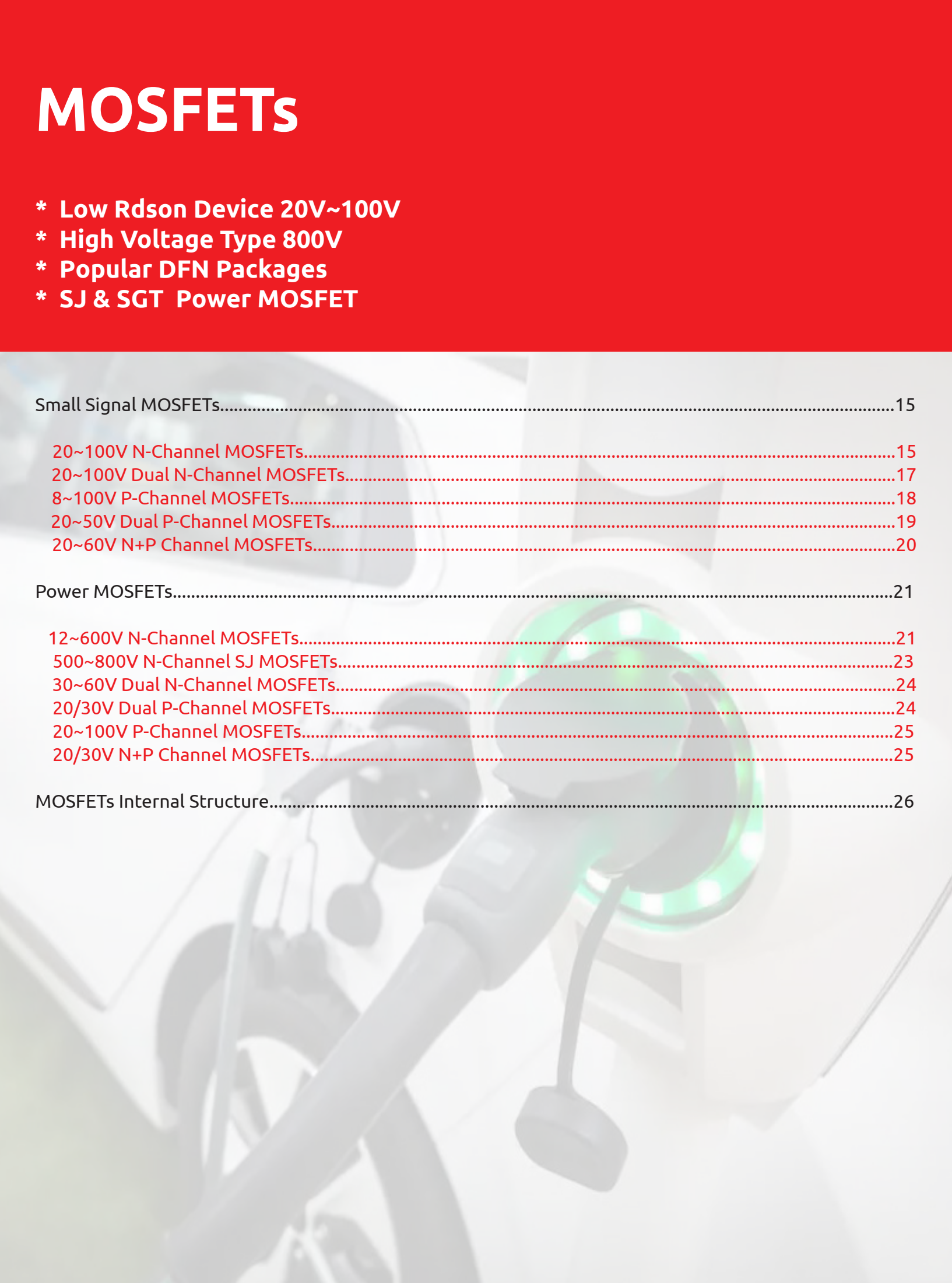


MOSFETs

- * Low Rdson Device 20V~100V
- * High Voltage Type 800V
- * Popular DFN Packages
- * SJ & SGT Power MOSFET



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Small Signal MOSFETs

20~100V N-Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (V/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
SI3134KA	SOT-723	N	0.15	20	±12	0.75		0.3	0.4	0.35	1.1	33	Yes	Fig.3
SI3134KEA	SOT-523	N	0.18	20	±12	0.75		0.3	0.4	0.35	1.1	33	Yes	Fig.3
SI3134KWA	SOT-323	N	0.2	20	±12	0.75		0.3	0.4	0.5	1.1	33	Yes	Fig.3
SI3134KL3A	DFN1006-3	N	0.9	20	±12	0.75		0.3	0.35	0.35	1.1	33	Yes	Fig.3
SI2302	SOT-23	N	1.25	20	±8.0	3		0.027	0.037	0.65	1.2	237	No	Fig.1
SI2302A	SOT-23	N	1.25	20	±8.0	3		0.072	0.11	0.65	1.2	237	No	Fig.1
SI2102A	SOT-323	N	120	20	±10	3		0.07	0.098	0.55	1	220	No	Fig.1
SI2300	SOT-23	N	1	20	±10	4.5		0.025	0.038	0.5	0.9	482	No	Fig.1
SI2312A	SOT-23	N	0.35	20	±8.0	5		0.025	0.033	0.5	0.9	865	No	Fig.1
SI2312	SOT-23	N	1.25	20	±8.0	5		0.0318	0.0356	0.45	1	865	No	Fig.1
SI3420A	SOT-23	N	1.25	20	±10	6		0.028	0.035	0.5	1	515	No	Fig.1
SI2312B	SOT-23	N	1.25	20	±10	6.8		0.021	0.03	0.5	0.9	500	No	Fig.1
SIL08N02	SOT23-6L	N	1.5	20	±10	8		0.017	0.021	0.45	1	900	No	Fig.11
2SK3019	SOT-523	N	0.15	30	±20	0.1			13	0.8	1.5	13	Yes	Fig.3
2SK3019A	SOT-523	N	0.15	30	±20	0.1		8		0.8	1.5	13	Yes	Fig.3
2SK3018	SOT-323	N	0.2	30	±20	0.1			13	0.8	1.5	13	Yes	Fig.3
SI3099	SOT-23	N	0.83	30	±12	1.1	0.408	0.518	0.8	0.5	1.5	61	Yes	Fig.3
SI2304	SOT-23	N	1	30	±20	2.5	0.065	0.09		1	2	240	No	Fig.1
SI2306	SOT-23	N	0.75	30	±20	3.16	0.047	0.065		1	3	305	No	Fig.1
SI3402	SOT-23	N	1.3	30	±12	4	0.055	0.07	0.11	0.6	1.4	390	No	Fig.1
SI3400	SOT-23	N	0.35	30	±12	5.8	0.035	0.04	0.052	0.7	1.4	1050	No	Fig.1
SI3404	SOT-23	N	1.2	30	±20	5.8	0.028	0.042		1	3	820	No	Fig.1
SI3404HE3	SOT-23	N	1.2	30	±20	5.8	0.028	0.042		1	3	820	No	Fig.1
SI3400A	SOT-23	N	1.3	30	±12	5.8	0.027	0.033	0.051	0.7	1.2	1155	No	Fig.1
SIL3400A	SOT23-6L	N	2	30	±12	5.8	0.032	0.038	0.045	0.7	1.4	1155	No	Fig.11
SIL08N03	SOT23-6L	N	1.6	30	±20	8	0.014	0.016		1	3	900	No	Fig.11
SI2318A	SOT-23	N	1.2	40	±20	5	0.045	0.06		0.8	1.8	330	No	Fig.1
BSS138W	SOT-323	N	0.3	50	±20	0.22	3.5	6		0.8	1.5	27	No	Fig.1
BSS138	SOT-23	N	0.35	50	±20	0.22	3.5	6		0.8	1.5	27	No	Fig.1
BSS138A	SOT-23	N	0.35	50	±20	0.22	1.6	2.5		0.8	1.45	22.8	Yes	Fig.3
BSS138HE3	SOT-23	N	0.35	50	±20	0.22	2.5	3		0.8	1.5	27	No	Fig.1
BSS138KT	SOT-523	N	0.25	50	±20	0.25	1.6	2.5		0.5	1.5	22.8	Yes	Fig.3
2N7002KT	SOT-523	N	0.15	60	±20	0.115	13.5			1	2	50	Yes	Fig.3
2N7002T	SOT-523	N	0.15	60	±20	0.115	13.5			1	2	50	No	Fig.1
2N7002	SOT-23	N	0.2	60	±20	0.115	5			1	2.5	50	No	Fig.1
2N7002HV	SOT-23	N	0.2	60	±20	0.115	7.5			1.6	1.8	50	No	Fig.1
2N7002W	SOT-323	N	0.2	60	±20	0.115	13.5			1	2	50	No	Fig.1
2N7002A	SOT-23	N	0.3	60	±30	0.115	3	4		1	2.5	50	No	Fig.1
2N7002KS	SOT-23	N	0.35	60	±20	0.3	2.2	3		1	2.5	27	Yes	Fig.3
2N7002KM	SOT-723	N	0.15	60	±20	0.34	4	4.5		1	2.5	40	Yes	Fig.3
2N7002KW	SOT-323	N	0.2	60	±20	0.34	5	5.3		1	2	40	Yes	Fig.3
2N7002KWA	SOT-323	N	0.2	60	±20	0.34	5	5.3		1	2	40	Yes	Fig.3
2N7002KWHE3	SOT-323	N	0.2	60	±20	0.34	2.5	3		1	2	40	Yes	Fig.3
2N7002K	SOT-23	N	0.35	60	±20	0.34	2.5	3		1	2.5	40	Yes	Fig.3

20~100V N-Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (V/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
2N7002KA	SOT-23	N	0.35	60	±20	0.34	5	5.3		1	2.5	35	Yes	Fig.3
2N7002KHE3	SOT-23	N	0.35	60	±20	0.34	2.5	3		1	2.5	40	Yes	Fig.3
2N7002KL3	DFN1006-3	N	0.1	60	±20	0.41	1.5	1.8		1.3	2.3	80	Yes	Fig.3
SI2310	SOT-23	N	1.2	60	±20	3	0.105	0.125		0.5	2	247	No	Fig.1
SI2310A	SOT-23	N	1.2	60	±20	3	0.105	0.125		0.5	1.5	247	No	Fig.1
SI2310B	SOT-23	N	1.2	60	±16	3	0.105	0.125		0.5	1.3	247	No	Fig.1
MCA03N06	SOT-89	N	1.7	60	±20	3	0.1	0.12		0.65	1.55	340	No	Fig.1
BSS123K	SOT-23	N	0.35	100	±20	0.17	6	9		1.5	2.5	60	Yes	Fig.3
SI2324A	SOT-23	N	1.2	100	±20	2	0.28	0.3		1	2	520	No	Fig.1
SI2392	SOT-23	N	1.2	100	±20	3	0.14	0.3		1	3	206	No	Fig.1

Small Signal MOSFETs

20~100V Dual N-Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (Y/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
SI3134KDWA	SOT-363	N+N	0.15	20	±12	0.75		0.3	0.4	0.5	1.1	33	Yes	Fig.7
SIX3134KA	SOT-563	N+N	0.18	20	±12	0.75		0.3	0.4	0.35	0.95	33	Yes	Fig.7
SIL2322A	SOT23-6L	N+N	1.25	20	±8.0	3		0.03	0.04	0.55	1.25	500	No	Fig.16
SIL2300	SOT23-6L	N+N	1.25	20	±10	4		0.025	0.032	0.45	1	620	No	Fig.28
SIL2300A	SOT23-6L	N+N	1.5	20	±10	7		0.018	0.022	0.45	1	900	No	Fig.28
UM6K1NA	SOT-363	N+N	0.3	30	±20	0.5	0.75	0.96		0.7	1.5	28	Yes	Fig.7
BSS138AKDW	SOT-363	N+N	0.35	50	±20	0.22	2	2.5	4.5	0.8	1.45	22.8	Yes	Fig.7
BSS138AKDW-TPQ2	SOT-363	N+N	0.35	50	±20	0.22	2	2.5	4.5	0.8	1.45	22.8	Yes	Fig.7
2N7002DW	SOT-363	N+N	0.15	60	±20	0.115	7			1	2.5	50	No	Fig.5
2N7002V	SOT-563	N+N	0.15	60	±20	0.115	5			1	2.5	50	No	Fig.5
2N7002KDW	SOT-363	N+N	0.15	60	±20	0.34	5	5.3		1	2.5	40	Yes	Fig.7
2N7002KV	SOT-563	N+N	0.15	60	±20	0.34	5	5.3		1	2.5	40	Yes	Fig.7
SIL2324A	SOT23-6L	N+N	1.5	100	±20	2	0.28	0.3		1	2	520	No	Fig.16

8~100V P-Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (Y/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
SI2305	SOT-23	P	1.4	-8	±8.0	-4.1		0.045	0.06	-0.55	-0.9	740	No	Fig.2
SI2333	SOT-23	P	1.1	-12	±8.0	-6		0.028	0.04	-0.4	-1	1275	No	Fig.2
SI3139KEA	SOT-523	P	0.15	-20	±12	-0.6		0.85	1.2	-0.35	-1.1	40	Yes	Fig.4
SI3139KWA	SOT-323	P	0.15	-20	±12	-0.6		0.85	1.2	-0.35	-1.1	40	Yes	Fig.4
SI2101A	SOT-323	P	0.45	-20	±10	-2		0.13	0.17	-0.4	-1	290	No	Fig.2
SI2301	SOT-23	P	1.25	-20	±8.0	-2.8		0.12	0.15	-0.45	-1	880	No	Fig.2
SI2301A	SOT-23	P	1	-20	±8.0	-2.8		0.12	0.15	-0.5	-0.9	880	No	Fig.2
SI2321	SOT-23	P	0.35	-20	±12	-2.9		0.057	0.076	-0.4	-0.9	715	No	Fig.2
SI2305B	SOT-23	P	1.4	-20	±10	-4.2		0.039	0.049	-0.5	-0.9	740	No	Fig.2
SI2305BHE3	SOT-23	P	1.4	-20	±10	-4.2		0.06	0.08	-0.5	-0.9	1010	No	Fig.2
SIL2305B	SOT23-6L	P	2	-20	±10	-5.4		0.06	0.08	-0.5	-0.9	740	No	Fig.10
SI3415BS	SOT-23	P	1.3	-20	±10	-5.6		0.042	0.055	-0.5	-0.9	1180	Yes	Fig.4
SI2307	SOT-23	P	1.1	-30	±20	-2.7	0.088	0.138		-1	-3	340	No	Fig.2
SI2303	SOT-23	P	1.3	-30	±20	-3	0.13	0.18		-1	-3	226	No	Fig.2
SI3407	SOT-23	P	1.3	-30	±20	-4.1	0.049	0.065		-1	-3	700	No	Fig.2
SI3407HE3	SOT-23	P	1.3	-30	±20	-4.1	0.06	0.087		-1	-3	700	No	Fig.2
SIL3407	SOT23-6L	P	1.6	-30	±20	-4.1	0.05	0.07		-1	-3	700	No	Fig.10
SI3401	SOT-23	P	1.3	-30	±12	-4.2	0.065	0.075	0.09	-0.7	-1.3	954	No	Fig.2
SI3401A	SOT-23	P	1.3	-30	±12	-4.2	0.06	0.07	0.085	-0.7	-1.3	1050	No	Fig.2
SI3401AHE3	SOT-23	P	1.2	-30	±12	-4.2	0.06	0.07	0.085	-0.7	-1.3	1050	No	Fig.2
SL3407	SOT-23-3L	P	1.5	-30	±20	-4.3	0.049	0.065		-1	-3	700	No	Fig.2
SL3401A	SOT-23-3L	P	1.5	-30	±12	-4.4	0.06	0.07	0.085	-0.7	-1.3	1050	No	Fig.2
SL3007	SOT-23-3L	P	1.9	-30	±20	-7	0.025	0.036		-1	-2.5	1500	No	Fig.2
BSS84	SOT-23	P	0.225	-50	±20	-0.13	8			-0.9	-2	30	No	Fig.2
BSS84KW	SOT-323	P	0.225	-50	±20	-0.13	8			-0.9	-2	22	Yes	Fig.4
BSS84K	SOT-23	P	0.225	-60	±20	-0.13	6	7		-0.8	-2.5	30	Yes	Fig.4
SL03P10	SOT-23-3L	P	0.83	-100	±20	-3	0.286	0.335		-1.1	-2	1010	No	Fig.2

Small Signal MOSFETs

20~50V Dual P-Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (Y/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
SI3139KDWA	SOT-363	P+P	0.15	-20	±12	-0.6		0.85	1.2	-0.35	-1.1	40	Yes	Fig.9
SIL2301	SOT23-6L	P+P	1.25	-20	±8.0	-2.3		0.09	0.125	-0.4	-1	405	No	Fig.15
SIL2623A	SOT23-6L	P+P	1.25	-30	±20	-3	0.09	0.115		-1	-2.5	365	No	Fig.15
BSS84DW	SOT-363	P+P	0.45	-50	±20	-0.16	8			-0.9	-2	30	NO	Fig.17

20~60V N+P Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (Y/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
SI3439KDWA	SOT-363	N+P	0.15	20,-20	±12	0.75,-0.6		0.3,0.85	0.4,1.2	0.35	1.1,-1.1	33,40	Yes	Fig.8
SIX3439KA	SOT-563	N+P	1.5	20,-20	±12	0.75,-0.6		0.3,0.85	0.4,1.2	0.35,-0.35	1.1,-1.1	33,40	Yes	Fig.8
SIL2308	SOT23-6L	N+P	1	20,-20	±8, ±12	5, -4		0.038, 0.09	0.045, 0.11	0.5, -0.5	1, -1	800	No	Fig.24
SIL3724A	SOT23-6L	N+P	2	30,-30	±20	4.5,-3.5	0.035,0.090	0.050,0.115		1.0,-1.0	2.5,-2.5	315, 365	No	Fig.24
BSS8402DW	SOT-363	N+P	0.2	60,-50	±20	0.115,-0.13	2, 8			1, -0.9	2.5, -2	50, 30	No	Fig.6

Power MOSFETs

12~600V N-Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (V/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
MCMN2014HE3	DFN2020-6LE	N	0.7	12	±8.0	15		0.009	0.011	0.4	1.1	1791	No	Fig.11
MCMN2012A	DFN2020-6JA	N	0.75	20	±10	12		0.015	0.018	0.35	1	1800	No	Fig.11
MCU30N02	DPAK	N	30	20	±10	30		0.007	0.009	0.45	1	1700	No	Fig.1
MCU60N02	DPAK	N	35	20	±10	60		0.006	0.0088	0.4	1	2450	No	Fig.1
MCU90N02	DPAK	N	45	20	±10	90		0.0045	0.005	0.4	1	3250	No	Fig.1
MCQ4406A	SOP-8	N	2.5	30	±20	12	0.012	0.015		1	2.5	950	No	Fig.23
MCM13N03	DFN2020-6LE	N	2.9	30	±20	13	0.012	0.015		1	2.5	1015	No	Fig.11
MCQ16N03	SOP-8	N	2.5	30	±20	16	0.012	0.016		1	3	1550	No	Fig.23
MCQ18N03	SOP-8	N	2.5	30	±20	18	0.007	0.01		1	2.5	2150	No	Fig.23
MCG30N03A	DFN3333	N	20	30	±20	30	0.01	0.013		1	2.5	1020	No	Fig.23
MCAC40N03A	DFN5060	N	35	30	±20	40	0.0075	0.0115		1	2.5	1050	No	Fig.23
MCG50N03	DFN3333	N	30	30	±20	50	0.006	0.008		1	2.5	2150	No	Fig.23
MCAC50N03	DFN5060	N	30	30	±20	50	0.0047	0.006		1	2.5	1620	No	Fig.23
MCU50N03A	DPAK	N	60	30	±20	50	0.0073	0.0115		1	2.2	1015	No	Fig.1
MCG65N03	DFN3333	N	75	30	±20	65	0.0032	0.004		1	2.5	4498	No	Fig.23
MCU80N03	DPAK	N	70	30	±20	80	0.004	0.006		0.8	2.5	1600	No	Fig.1
MCU80N03A	DPAK	N	45	30	±20	80	0.0055	0.008		1	2.5	2150	No	Fig.1
MCAC10H03A	DFN5060	N	49	30	±20	100	0.003	0.004		1	2.5	3865	No	Fig.23
MCAC150N03A	DFN5060	N	75	30	±20	150	0.002	0.003		1	2.5	4498	No	Fig.23
MCG20N04	DFN3333	N	21	40	±20	20	0.014	0.0185		1	2.5	750	No	Fig.23
MCG35N04A	DFN3333	N	40	40	±20	35	0.008	0.013		1	2.5	1860	No	Fig.23
MCU60N04A	DPAK	N	70	40	±20	60	0.007	0.0096		0.9	2	1650	No	Fig.1
MCU120N04	DPAK	N	110	40	±20	120	0.0035	0.0048		1	2.5	4645	No	Fig.1
MCAC130N04	DFN5060	N	115	40	±20	130	0.00175	0.0025		1	2.5	7140	No	Fig.23
MCQ4438	SOP-8	N	1.25	60	±20	8.2	0.022	0.036		1	3	2300	No	Fig.23
MCQ12N06	SOP-8	N	3.1	60	±20	12	0.009	0.013		1.1	2.5	1988	No	Fig.17
MCU20N06B	DPAK	N	1.25	60	±20	20	0.045			1	3	500	No	Fig.1
MCAC30N06Y	DFN5060	N	30	60	±20	30	0.02	0.022		1	2.5	1552	No	Fig.23
MCG53N06A	DFN3333	N	45	60	±20	53	0.0082	0.012		1	2.5	1525	No	Fig.23
MCAC53N06Y	DFN5060	N	70	60	±20	53	0.0082	0.012		1.1	2.5	1988	No	Fig.23
MCAC80N06Y	DFN5060	N	85	60	±20	80	0.0042	0.0052		1.1	2.5	3980	No	Fig.23
MCU80N06A	DPAK	N	68	60	±20	80	0.008	0.011		1.2	2.2	1990	No	Fig.1
MCAC85N06KY	DFN5060	N	110	60	±20	85	0.0037	0.005		1	2.5	4650	Yes	Fig.31
MCU90N06A	DPAK	N	110	60	±20	90	0.0072	0.0085		1	2.5	5170	No	Fig.1
MCP90N06Y	TO-220AB(H)	N	83	60	±20	90	0.0075	0.01		1	2.5	2000	No	Fig.1
MCAC95N06Y	DFN5060	N	120	60	±20	95	0.0025	0.0034		1.2	2.2	5950	No	Fig.23
MCAC95N06YB	DFN5060	N	120	60	±20	95	0.0029			2	4	5950	No	Fig.23
MCB150N06KY	D2-PAK	N	147	60	±20	150	0.0035	0.0048		1	2.5	4650	Yes	Fig.3
MCB200N06Y	D2-PAK	N	260	60	±20	200	0.0026	0.0036		1.2	2.2	5950	No	Fig.1
MCB200N06YA	D2-PAK	N	260	60	±20	200	0.0032			2.2	3.8	4165	No	Fig.1
MCP200N06Y	TO-220AB(H)	N	260	60	±20	200	0.0032			2	4	4165	No	Fig.1
MCAC95N065Y	DFN5060	N	120	65	±20	95	0.0025	0.0034		1.2	2.2	5950	No	Fig.23
MCAC100N08Y	DFN5060	N	51	80	±20	100	0.0045			2	4	5469	No	Fig.23
MCT04N10B	SOT-223	N	72	100	±20	4	0.105	0.12		1.1	3	1143	No	Fig.1

12~600V N-Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (V/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
MCT04N10B	SOT-223	N	72	100	±20	4	0.105	0.12		1.1	3	1143	No	Fig.1
MCU15N10A	DPAK	N	34	100	±20	15	0.11	0.12		1.1	3	800	No	Fig.1
MCQ12N10Y	SOP-8	N	3.1	100	±20	12	0.017			1	3	2270	No	Fig.23
MCQ15N10YA	SOP-8	N	3.8	100	±20	15	0.0095	0.0125		1	3	2270	No	Fig.23
MCU20N10A	DPAK	N	47	100	±20	20	0.045	0.06		1.2	2.5	2014	No	Fig.1
MCU20N10	DPAK	N	47	100	±20	20	0.048	0.053		1	3	2014	No	Fig.1
MCAC38N10Y	DFN5060	N	59	100	±20	38	0.0175	0.0215		1	2.5	1051	No	Fig.23
MCU45N10	DPAK	N	72	100	±20	45	0.017	0.0215		1	3	1135	No	Fig.1
MCU45N10HE3	DPAK	N	72	100	±20	45	0.017	0.0215		1	3	1135	No	Fig.1
MCAC60N10Y	DFN5060	N	88	100	±20	60	0.0086			2.2	3.4	2431	No	Fig.23
MCAC60N10YA	DFN5060	N	88	100	±20	60	0.0086	0.013		1.3	2.5	2270	No	Fig.23
MCB70N10YB	D2-PAK	N	125	100	±20	70	0.0086			2	4	2270	No	Fig.1
MCP75N10Y	TO-220AB(H)	N	125	100	±20	75	0.0086			2	4	2270	No	Fig.1
MCAC90N10Y	DFN5060	N	120	100	±20	90	0.0052			2	4	4600	No	Fig.23
MCB130N10Y	D2-PAK	N	192	100	±20	130	0.0046			1.2	4	6124.6	No	Fig.1
MCB130N10YA	D2-PAK	N	260	100	±20	130	0.0046			2	4	4600	No	Fig.1
MCB180N10Y	D2-PAK	N	357	100	±20	180	0.0033			2	4	9200	No	Fig.1
MCU20N15A	DPAK	N	50	150	±20	20	0.059			2	4	1158	No	Fig.1
MCU05N60A	DPAK	N	1.25	600	±30	4.5	2.5			2	4	670	No	Fig.1

Power MOSFETs

500~800V N-Channel SJ MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (Y/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
MSJAC11N50B	DFN5060	N	83	500	±30	11	0.38			2.5	3.5	702	No	Fig.23
MSJU07N65A	DPAK	N	63	650	±30	7	0.6			2	4	545	No	Fig.1
MSJU11N65A	DPAK	N	83.3	650	±30	11	0.38			2	4	763	No	Fig.1
MSJP11N65A	TO-220	N	83.3	650	±30	11	0.38			2	4	763	No	Fig.1
MSJPF11N65A	TO-220F	N	31.3	650	±30	11	0.38			2	4	763	No	Fig.1
MSJB06N80A	D2-PAK	N	35	800	±30	6	1.2			2.5	4.5	349	Yes	Fig.3
MSJPF06N80A	TO-220F	N	22	800	±30	6	1.2			2.5	4.5	349	Yes	Fig.3
MSJB17N80	D2-PAK	N	181	800	±30	17	0.29			2	4	1830	No	Fig.1

30~60V Dual N-Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (V/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
MCM3400A	DFN2020-6L	N+N	1.4	30	±12	5	0.032	0.038	0.045	0.7	1.5	1155	No	Fig.5
MCQD08N03A	SOP-8	N+N	3	30	±20	8.5	0.023	0.032		1	2.2	490	No	Fig.19
MCQD12N03A	SOP-8	N+N	2.5	30	±20	12	0.012	0.015		1	2.5	950	No	Fig.19
MCGD25N04	DFN3333-D	N+N	3	40	±20	25	0.018	0.024		1	2.5	750	No	Fig.19
MCQD05N06	SOP-8	N+N	3	60	±20	5	0.044	0.049		1	2.5	800	No	Fig.19

20/30V Dual P-Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (V/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
MCM2301	DFN2020-6L	P+P	1.4	-20	±10	-3.8		0.07	0.09	-0.5	-0.9	880	No	Fig.17
MCQ4953	SOP-8	P+P	2.5	-30	±20	-5	0.06	0.09		-1	-2.5		No	Fig.18
MCQ7328	SOP-8	P+P	1.4	-30	±20	-8	0.021	0.032		-1	-2.5	2675	No	Fig.18

Power MOSFETs

20~100V P-Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (V/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
MCM1216A	DFN2020-6JA	P	18	-20	±10	-16		0.017	0.021	-0.4	-1	2050	No	Fig.10
MCG55P02A	DFN3333	P	38	-20	±10	-55		0.0083	0.01	-0.4	-1	6358	No	Fig.30
MCQ9435	SOP-8	P	1.4	-30	±20	-5.1	0.06	0.105		-1	-2		No	Fig.21
MCQ4435A	SOP-8	P	1.4	-30	±20	-10	0.024	0.035		-1	-3	1350	No	Fig.21
MCQ4407B	SOP-8	P	3.2	-30	±25	-12	0.0125	0.025		-1.2	-2.8	2050	No	Fig.21
MCG20P03	DFN3333	P	21	-30	±20	-20	0.02	0.027		-1	-2.5	1750	No	Fig.21
MCG30P03	DFN3333	P	32	-30	±25	-30	0.015	0.025		-1.2	-2.8	2050	No	Fig.21
MCU45P03A	DPAK	P	75	-30	±25	-45	0.008	0.013		-1.2	-2.8	2152	No	Fig.2
MCG50P03	DFN3333	P	83	-30	±25	-50	0.0062	0.011		-1.2	-2.8	6464	No	Fig.21
MCAC50P03B	DFN5060	P	83	-30	±25	-50	0.0055	0.0095		-1.2	-2.8	6464	No	Fig.21
MCG25P06Y	DFN3333	P	60	-60	±20	-25	0.05	0.065		-1.5	-2.7	1100	No	Fig.21
MCU30P06Y	DPAK	P	72	-60	±20	-30	0.055	0.065		-1.5	-2.7	1050	No	Fig.2
MCAC80P06Y	DFN5060	P	120	-60	±18	-80	0.008			-2	-4	5450	No	Fig.21
MCU80P06Y	DPAK	P	120	-60	±18	-80	0.0084			-2	-4	5450	No	Fig.2
MCQ05P10Y	SOP-8	P	3.1	-100	±20	-4.5	0.11	0.12		-1	-2.5	1051	No	Fig.21
MCU18P10Y	DPAK	P	70	-100	±20	-18	0.11	0.13		-1	-2.5	1050	No	Fig.2
MCAC25P10Y	DFN5060	P	88	-100	±20	-25	0.056	0.062		-1	-2.5	2100	No	Fig.21
MCU28P10Y	DPAK	P	96	-100	±20	-28	0.052	0.056		-1	-2.5	2100	No	Fig.2
MCB40P10Y	D2-PAK	P	125	-100	±20	-40	0.056	0.062		-1	-2.5	2100	No	Fig.2

20/30V N+P Channel MOSFETs

Part Number	Package	Channel	Power Rating	Drain-Source Voltage	Gate Source Voltage	Drain Current	Static Drain-Source On-Resistance			Gate Threshold Voltage (Min)	Gate Threshold Voltage (Max)	Input Capacitance	ESD Diodes (V/N)	Internal Structure
			P _D (W)	V _{DS} (V)	V _{GS} (V)	I _D (A)	R _{DS(ON)} (Ω) @10V	R _{DS(ON)} (Ω) @4.5V	R _{DS(ON)} (Ω) @2.5V	V _{GS(th)} (V)	V _{GS(th)} (V)	C _{iss} (pF)		
MCMNP2065	DFN2020-6L	N+P	2.2,1.8	20,-20	±10	6.0,-6.0		0.025,0.042	0.032,0.055	0.4,-0.4	1.0,-1.0	418, 1010	No	Fig.6
MCQ4503B	SOP-8	N+P	2	30,-30	±12	5.6,-4.4	0.025,0.055	0.031,0.066		0.65,-0.6	1.5,-1.4	535, 680	No	Fig.20
MCQ07NP03A	SOP-8	N+P	1.9	30,-30	±20	7.0,-7.0	0.018,0.023	0.030,0.034		1.0,-1.0	2.2,-2.5	526, 1497	No	Fig.20

Internal Structure

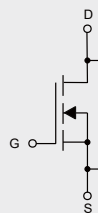


Fig.1

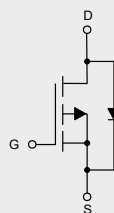


Fig.2

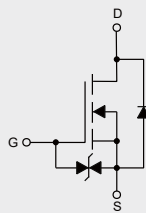


Fig.3

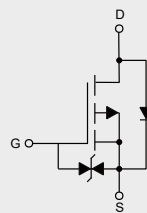


Fig.4

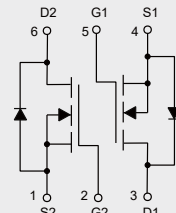


Fig.5

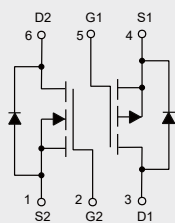


Fig.6

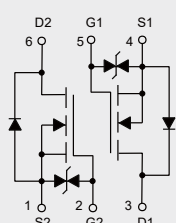


Fig.7

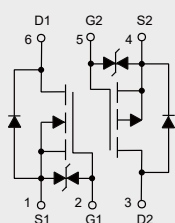


Fig.8

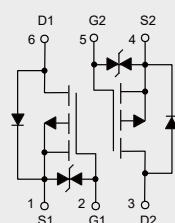


Fig.9

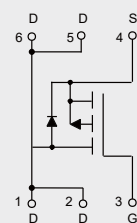


Fig.10

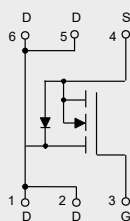


Fig.11

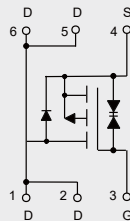


Fig.12

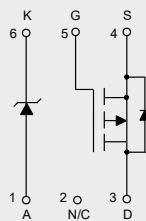


Fig.13

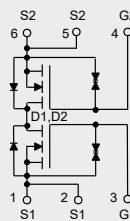


Fig.14

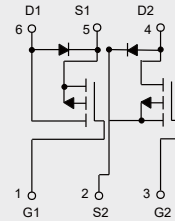


Fig.15

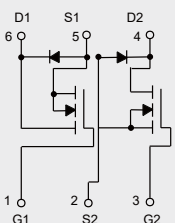


Fig.16

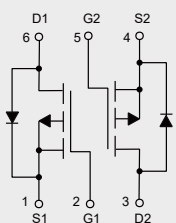


Fig.17

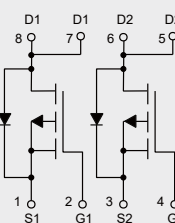


Fig.18

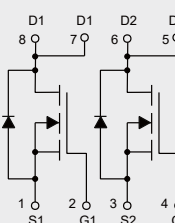


Fig.19

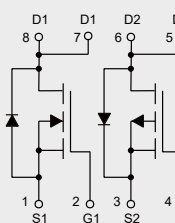


Fig.20

Internal Structure

Internal Structure

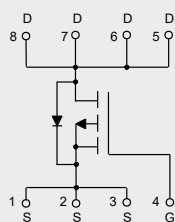


Fig.21

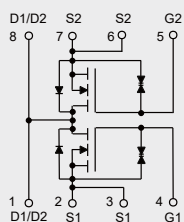


Fig.22

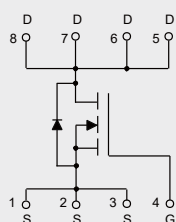


Fig.23

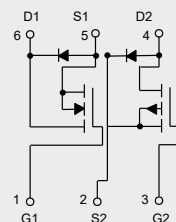


Fig.24

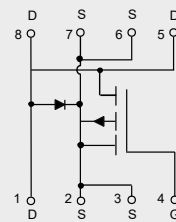


Fig.25

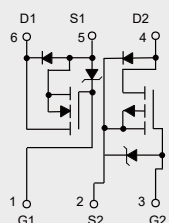


Fig.26

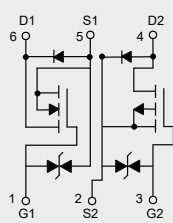


Fig.27

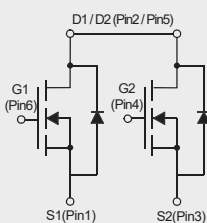


Fig.28

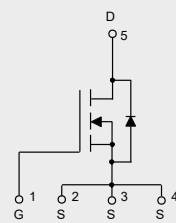


Fig.29

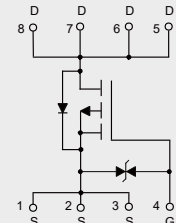


Fig.30

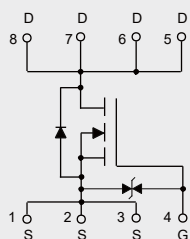


Fig.31